N-channel 100 V, 40 mOhm, standard level Trench MOSFET in MLPAK33

21 September 2023

Product data sheet

1. General description

General purpose MOSFET for standard applications, 17 A, standard level N-channel enhancement mode Power MOSFET in MLPAK33 package.

2. Features and benefits

- · Standard level compatibility
- Trench MOSFET technology
- Thermally efficient package in a small form factor (3.3 mm x 3.3 mm footprint)

3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- · Home appliance
- Motor drive
- Load switching
- LED lighting

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	17	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	21	W
Tj	junction temperature			-55	-	150	°C
Static charac	teristics				'		'
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 9$		-	36	40	mΩ
Dynamic cha	racteristics				'		'
Q_{GD}	gate-drain charge	I _D = 5 A; V _{DS} = 50 V; V _{GS} = 10 V;		-	1.5	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>		-	6.6	-	nC
Avalanche ru	ggedness						
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 9.5 A; $V_{sup} \le 100$ V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	[1]	-	-	9	mJ



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain d	Source-drain diode						
Q _r		$I_S = 5 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s; } V_{GS} = 0 \text{ V;}$ $V_{DS} = 50 \text{ V; } T_j = 25 \text{ °C; } \underline{\text{Fig. 15}}$	[2]	-	19	-	nC

- [1] Protected by 100% test
- [2] includes capacitive recovery

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source		
3	S	source		D ⊥
4	G	gate]	
5	D	drain	$G \longrightarrow G$	G—(F)
6	D	drain	l Laaad	mbb076 S
7	D	drain	8 7 6 5 MI DAK 22 (SOT 2002 4)	
8	D	drain	MLPAK33 (SOT8002-1)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PXN040-100QS		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1		

7. Marking

Table 4. Marking codes

Type number	Marking code
PXN040-100QS	7AS

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	100	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	21	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	17	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	10	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3	-	66	Α
T _{stg}	storage temperature		-55	150	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	150	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain	diode					'
Is	source current	T _{mb} = 25 °C		-	17	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	66	Α
Avalanche ru	ggedness					'
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 9.5 A; $V_{sup} \le 100 \text{ V}$; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	[1]	-	9	mJ
I _{AS}	non-repetitive avalanche current	$T_{j(init)} = 25 ^{\circ}C$	[1]	-	9.5	Α

[1] Protected by 100% test

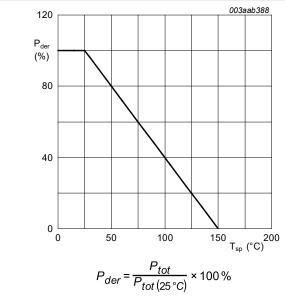


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

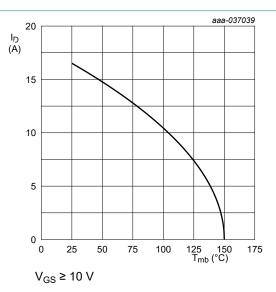


Fig. 2. Continuous drain current as a function of mounting base temperature

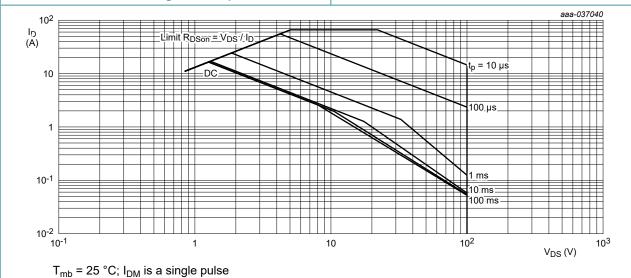


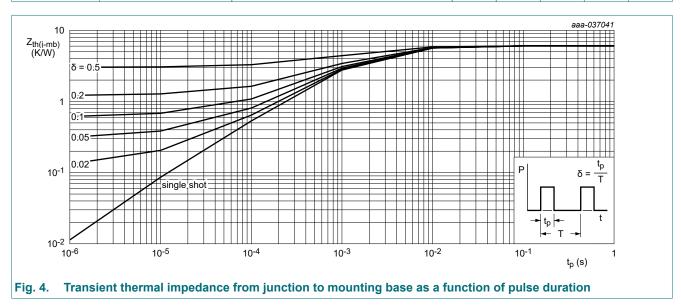
Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	5	6	K/W



10. Characteristics

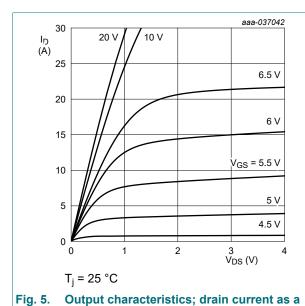
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics				<u> </u>	'
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	-	100	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 8	2	3	4	V
		I _D = 0.25 mA; V _{DS} =V _{GS} ; T _j = 150 °C	-	1.9	-	V
		$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	3.5	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-8.7	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 150 °C	-	-	3	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 9</u>	-	36	40	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 150 ^{\circ}\text{C};$ Fig. 10	-	-	76	mΩ
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	0.6	-	Ω

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic ch	naracteristics						
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>		-	6.6	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$		-	5.5	-	nC
Q _{GS}	gate-source charge	I _D = 5 A; V _{DS} = 50 V; V _{GS} = 10 V;		-	2.3	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 11; Fig. 12</u>		-	1.3	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge			-	1	-	nC
Q _{GD}	gate-drain charge	1		-	1.5	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 5 \text{ A}; V_{DS} = 50 \text{ V}; T_j = 25 \text{ °C}; Fig. 11; Fig. 12}$		-	5.2	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz;		-	351	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>		-	114	-	pF
C _{rss}	reverse transfer capacitance	1		-	6	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 10 \Omega; V_{GS} = 10 \text{ V};$		-	3.3	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$		-	2.1	-	ns
t _{d(off)}	turn-off delay time			-	5.6	-	ns
t _f	fall time			-	4.4	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	8.8	-	nC
Source-drai	in diode						
V _{SD}	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 14$		-	0.86	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;		-	28	-	ns
Q _r	recovered charge	V _{DS} = 50 V; T _j = 25 °C; <u>Fig. 15</u>	[1]	-	19	-	nC

[1] includes capacitive recovery



function of drain-source voltage; typical values

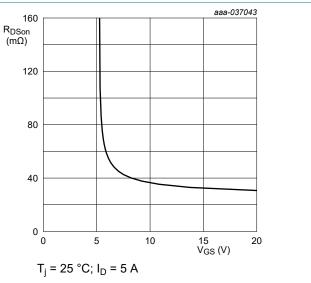


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

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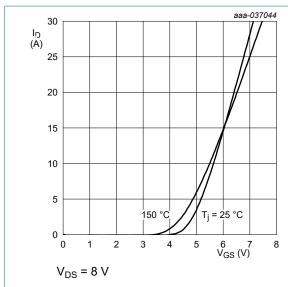


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

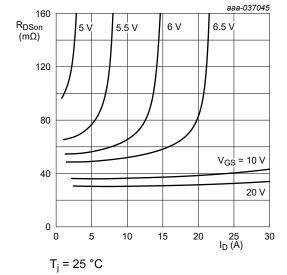


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

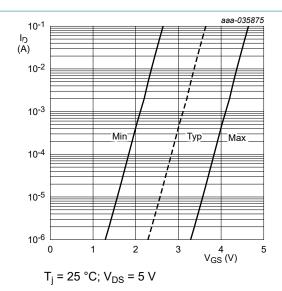


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

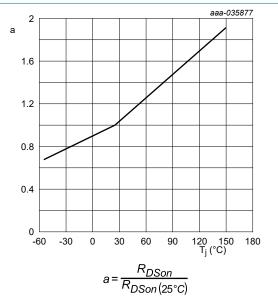


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

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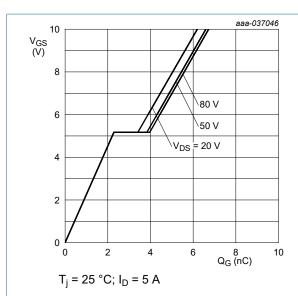


Fig. 11. Gate-source voltage as a function of gate charge; typical values

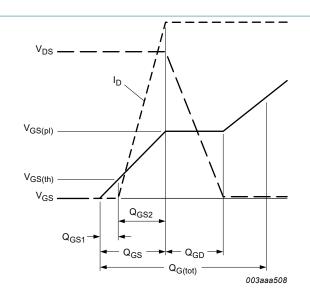


Fig. 12. Gate charge waveform definitions

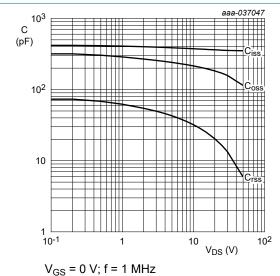
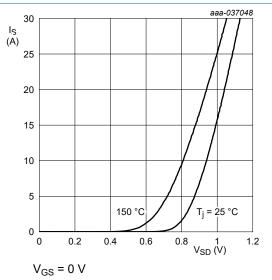


Fig. 13. Input, output and reverse transfer capacitances | Fig. 14. Source-drain (diode forward) current as a as a function of drain-source voltage; typical values



function of source-drain (diode forward) voltage; typical values

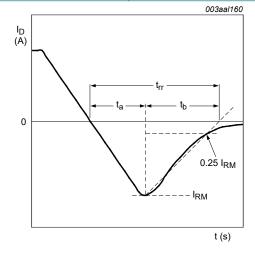


Fig. 15. Reverse recovery timing definition

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11. Package outline

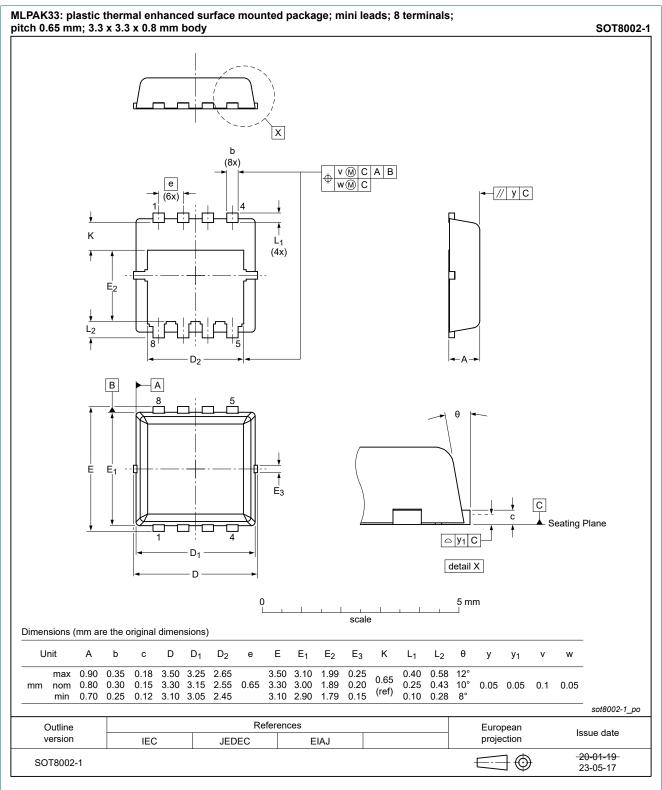
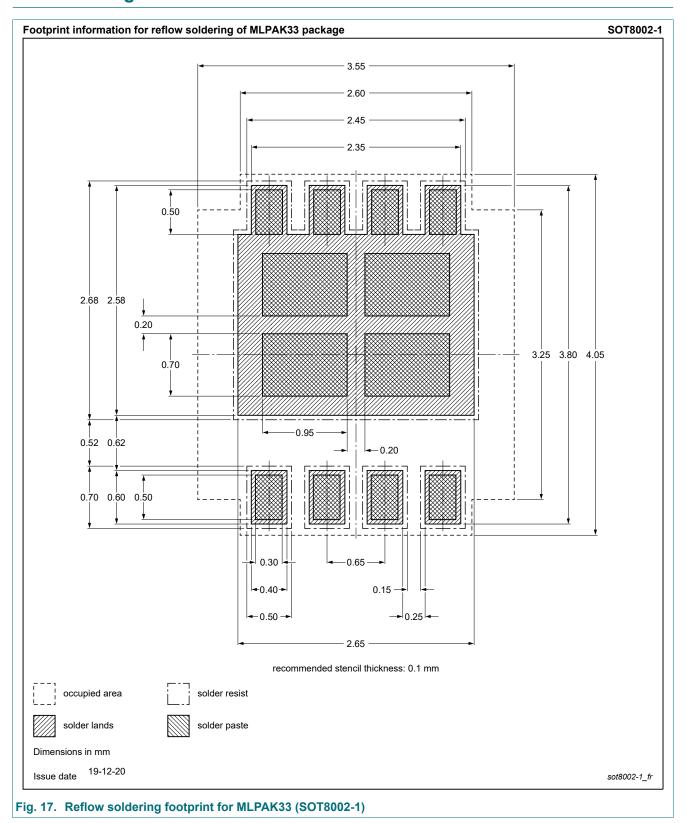


Fig. 16. Package outline MLPAK33 (SOT8002-1)

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12. Soldering



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13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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